

### Description

The NEC μPD4168 is an 8,192 word by 8-bit NMOS XRAM designed to operate from a single +5V power supply. The NEC μPD4168 is termed an XRAM because it incorporates some of the best features of both SRAMs (Non-multiplexed addresses, simple interface requirements) and DRAMs (the one-transistor core cell provides high density at low cost). The negative voltage substrate bias is internally generated and provides automatic and transparent operation.

The incorporation of an internal refresh address counter and refresh multiplexer allows the user to select one of three refresh modes. The self-refresh mode provides transparent refresh without system overhead. Internal latches for address, data, and chip select allow for use in systems incorporating multiplexed address/data buses.

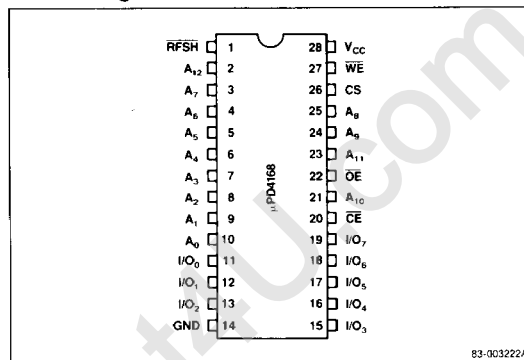
### Features

- 8,192 words by 8-bit organization
- Single +5V ± 10% power supply
- On-chip substrate bias generator
- Fast access times
- Low power dissipation:  
28 mW max-Standby  
19 mW max-Self refresh
- TTL-compatible
- 28-pin SRAM/ROM/EPROM compatible package
- Built-in refresh multiplexer and refresh address counter
- Power-down self-refresh mode
- Automatic precharge allows cycle time to be independent of system skews
- Latched address, CS, and OE functions allow use on multiplexed address/data bus
- Read, early write, late write, external refresh, pulse refresh, and self-refresh cycles

### Performance Ranges

Device	t <sub>CEA</sub>	t <sub>DEA</sub>	t <sub>C</sub>	I <sub>CC1</sub>
μPD4168C-12	120 ns	45 ns	220 ns	65 mA
μPD4168C-15	150 ns	55 ns	260 ns	60 mA
μPD4168C-20	200 ns	70 ns	330 ns	55 mA

### Pin Configuration



### Pin Identification

No.	Symbol	Function
1	RFSH	Internal refresh
2-10, 21, 23-25	A <sub>0</sub> -A <sub>12</sub>	Address inputs
11-13, 15-19	I/O <sub>0</sub> -I/O <sub>7</sub>	Data in / out
14	GND	Ground
20	CE	Chip enable
22	OE	Output enable
26	CS	Chip select
27	WE	Write enable
28	V <sub>CC</sub>	+5 V power supply

### Pin Functions

#### RFSH (Refresh Input)

A built-in refresh control circuit enables this input. Two refresh modes are available: pulse refresh, using the RFSH input as a clock input, and power-down self-refresh, using the RFSH input as logic level input. RFSH is high (inactive) during normal read and write cycles.

#### A<sub>0</sub>-A<sub>12</sub> (Address Inputs)

The μPD4168 requires 13 address inputs to select a word of data. Because these address inputs are internally read onto the chip at the falling edge of a CE clock pulse, the CE clock determines their address setup and hold times. Inputs A<sub>0</sub>-A<sub>6</sub> perform external refresh.

**I/O<sub>0</sub>-I/O<sub>7</sub> (Data Inputs/Outputs)**

Common I/O pins require  $\overline{WE}$  and  $\overline{OE}$  to control data. The  $\overline{CE}$  clock and  $\overline{WE}$  determine the data setup and hold times ( $t_{DSC}$ ,  $t_{DHC}$ ,  $t_{DSW}$ ,  $t_{DHW}$ ) for these pins during a memory write cycle;  $\overline{OE}$  determines the access time ( $t_{OEA}$ ) during a read cycle.

**GND (Ground)**

All voltages are referenced to GND.

**$\overline{CE}$  (Chip Enable)**

The chip enable clock initiates read/write cycles and external refresh cycles. It allows addresses, CS, and (during an early write cycle) data inputs to be internally read onto the chip.

**$\overline{OE}$  (Output Enable)**

$\overline{OE}$  controls the output timing for I/O<sub>0</sub>-I/O<sub>7</sub>. Access time ( $t_{CEA}$ ,  $t_{OEA}$ ) is determined by the  $\overline{CE}$  clock or by the  $\overline{OE}$  input, according to  $\overline{OE}$  input timing.

**CS (Chip Select)**

When CS is high (active) while the  $\overline{CE}$  clock is enabled, the μPD4168 can perform read/write operations. If CS is latched low (inactive) while the  $\overline{CE}$  clock is enabled, I/O<sub>0</sub>-I/O<sub>7</sub> remain in the high-impedance state, regardless of the status of  $\overline{WE}$  and  $\overline{OE}$ .

**$\overline{WE}$  (Write Enable)**

$\overline{WE}$  controls read/write operations.  $\overline{WE}$  input timing determines whether a write cycle is an early write or a late write.

**VCC (Power Supply)**

+5 V power supply.

**μPD4168 Functional Modes**

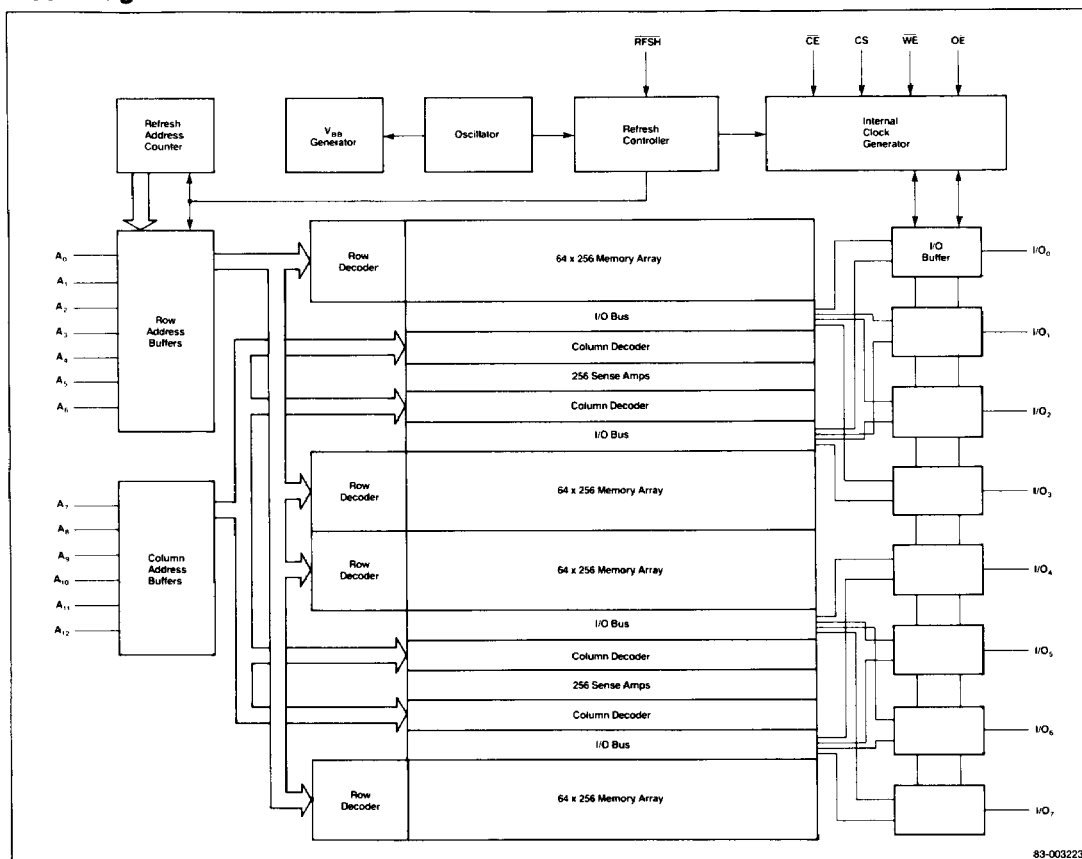
Mode	RFSH	$\overline{CE}$	CS	$\overline{WE}$	$\overline{OE}$	I/O	Comments
Read cycle	H	C'	H	H	L	Data out	$\overline{OE}$ : low logic level or clock pulse
Early write	H	C'	H	L	H	Data in	
Late Write	H	C'	H	C'	H	Data in	
External refresh	H	C'	H	H	H	High-Z	
	H	C'	L	X	X	High-Z	Standby
Pulse refresh	C'	H	X	X	X	High-Z	
	C'	C'	H	H	H	High-Z	After external refresh cycle
	C'	C'	H	H	L	(Note 1)	After read cycle
	C'	C'	H	L	H	Data in	After early write cycle
Power down self-refresh	C'	C'	H	C'	H	Data in	After late write cycle
	L	H	X	X	X	High-Z	
Standby	H	H	X	X	X	High-Z	

H = V<sub>IH</sub>, L = V<sub>IL</sub>, C' = negative edge of clock pulse, X = V<sub>IH</sub> or V<sub>IL</sub>

**Note:**

(1) Depends on previous cycle

## Block Diagram



### Absolute Maximum Ratings

Voltage on any pin relative to GND	-1.0 to +7.0 V
Operating temperature, T <sub>OPR</sub>	0 to +70°C
Storage temperature, T <sub>STG</sub>	-55 to +125°C
Short circuit output current, I <sub>OS</sub>	50 mA
Power dissipation, P <sub>D</sub>	1W

**Comment:** Exposing the device to stresses above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational sections of the specification. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### DC Characteristics

T<sub>A</sub> = 0 to +70°C; V<sub>CC</sub> = 5V ± 10%

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V	Referenced to GND
Input voltage, low	V <sub>IL</sub>	-1.0		0.8	V	Referenced to GND
Input voltage, high	V <sub>IH</sub>	2.4		5.5	V	Referenced to GND
Output voltage, low	V <sub>OL</sub>	0		0.4	V	I <sub>OL</sub> = 2 mA

**DC Characteristics (cont)**

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Output voltage, high	V <sub>OH</sub>	2.4		V <sub>CC</sub>	V	I <sub>OH</sub> = -1 mA
Average V <sub>CC</sub> supply current, active	I <sub>CC1</sub>			65	mA	t <sub>C</sub> = 220 ns
				60	mA	t <sub>C</sub> = 260 ns
				55	mA	t <sub>C</sub> = 330 ns
Standby current	I <sub>CC2</sub>			5	mA	$\overline{CE} \geq V_{IH} \text{ min,}$ RFSH $\geq V_{IH} \text{ min}$
Self-refresh average current	I <sub>CC3</sub>			3.5	mA	RFSH $\leq V_{IL} \text{ max}$
Input leakage current	I <sub>I(L)</sub>	-10		10	μA	V <sub>IN</sub> = 0 to 5.5 V; others = 0 V
Output leakage current	I <sub>O(L)</sub>	-10		10	μA	V <sub>OUT</sub> = 0 to 5.5 V; D <sub>OUT</sub> = High-Z

**Capacitance**

T<sub>A</sub> = 0 to +70°C, V<sub>CC</sub> = 5.0 V ± 10%

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Input capacitance	C <sub>I</sub>			10	pF	f = 1 MHz
Data I/O capacitance	C <sub>I/O</sub>			10	pF	f = 1 MHz

**AC Characteristics**

T<sub>A</sub> = 0 to +70°C, V<sub>CC</sub> = 5 V ± 10%

Parameter	Symbol	Limits						Unit	Test Conditions
		μPD4168-12		μPD4168-15		μPD4168-20			
		Min	Max	Min	Max	Min	Max		
Average V <sub>CC</sub> supply current, active	I <sub>CC1</sub>		65		60		55	mA	t <sub>C</sub> = t <sub>C</sub> (min)
Read, write, or refresh cycle time	t <sub>C</sub>		220		260		330	ns	
Access time from $\overline{CE}$	t <sub>CEA</sub>		120		150		200	ns	(Note 5)
Data off time from $\overline{CE}$	t <sub>CEZ</sub>		30		35		45	ns	(Note 6)
Access time from $\overline{OE}$	t <sub>OEA</sub>		45		55		70	ns	(Note 5)
Data off time from $\overline{OE}$	t <sub>OEZ</sub>		30		35		45	ns	(Note 6)
$\overline{CE}$ pulse width	t <sub>CE</sub>	120	10000	150	10000	200	10000	ns	
$\overline{CE}$ precharge time	t <sub>p</sub>	90		100		120		ns	
Address setup time to $\overline{CE}$	t <sub>ASC</sub>	0		0		0		ns	
Address hold time from $\overline{CE}$	t <sub>AHC</sub>	35		45		55		ns	
CS setup time to $\overline{CE}$	t <sub>CSC</sub>	0		0		0		ns	
CS hold time from $\overline{CE}$	t <sub>CHC</sub>	35		45		55		ns	
Data setup time to $\overline{CE}$ , early write	t <sub>DSC</sub>	-10		-10		-10		ns	
Data hold time from $\overline{CE}$ , early write	t <sub>DHC</sub>	90		100		120		ns	
Data setup time to $\overline{WE}$ , late write	t <sub>DSW</sub>	0		0		0		ns	
Data hold time from $\overline{WE}$ , late write	t <sub>DHW</sub>	50		60		70		ns	
$\overline{WE}$ setup time to $\overline{CE}$ , early write	t <sub>WSC</sub>	-30		-30		-30		ns	(Note 7)
$\overline{WE}$ hold time from $\overline{CE}$ , early write	t <sub>WHC</sub>	90		100		125		ns	
$\overline{WE}$ pulse duration	t <sub>WD</sub>	60		70		90		ns	
$\overline{CE}$ hold time from $\overline{WE}$ , late write	t <sub>CHW</sub>	90		105		135		ns	
$\overline{WE}$ setup time to $\overline{CE}$ , read cycle	t <sub>RCS</sub>	0		0		0		ns	
$\overline{WE}$ hold time from $\overline{CE}$ , read cycle	t <sub>RCH</sub>	0		0		0		ns	
$\overline{CE}$ hold time from $\overline{OE}$ , read cycle	t <sub>CHO</sub>	45		55		70		ns	
$\overline{OE}$ setup time to $\overline{CE}$ , write cycle	t <sub>OES</sub>	0		0		0		ns	
$\overline{OE}$ hold time from $\overline{CE}$ , write cycle	t <sub>OEH</sub>	0		0		0		ns	

## AC Characteristics (cont)

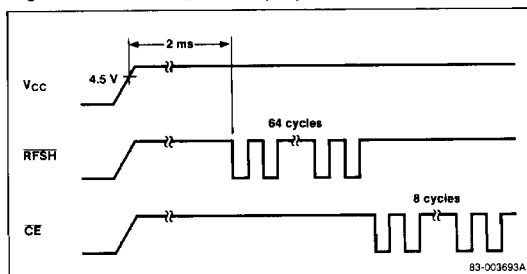
$T_A = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5\text{V} \pm 10\%$

Parameter	Symbol	Limits						Unit	Test Conditions
		μPD4168-12		μPD4168-15		μPD4168-20			
		Min	Max	Min	Max	Min	Max		
CE delay to RFSH, pulse refresh	$t_{CRD}$	50		65		80		ns	
RFSH pulse width, pulse refresh	$t_{RDP}$	50	4000	65	4000	80	4000	ns	
RFSH recovery time, pulse refresh	$t_{RPR}$	90		100		120		ns	
RFSH pulse width, self refresh	$t_{RDS}$	40		40		40		μs	(Note 8)
RFSH recovery time, self refresh	$t_{RSR}$	2		2		2		μs	
CE hold time from RFSH, self refresh	$t_{CSH}$	40		40		40		μs	
CE setup time to RFSH, self refresh	$t_{CSS}$	35		40		50		ns	
Transition time, rise and fall	$t_T$	3	50	3	50	3	50	ns	(Note 4)
Refresh period	$t_{REF}$		2		2		2	ms	
RFSH precharge time	$t_{RP}$	90		100		120		ns	
OE lead time to refresh cycle	$t_{OEL}$	170		210		260		ns	
WE lead time to refresh cycle	$t_{WEL}$	170		210		260		ns	
RFSH setup time to CE	$t_{RC}$	280		320		410		ns	

### Note:

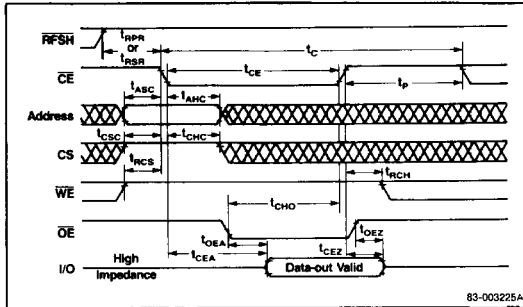
- (1) All voltages referenced to GND (0 V).
- (2) An initial pause of 2 ms is required after power up, followed by any 8 CE cycles and 64 RFSH cycles before proper device operation is achieved. Read, write, and external refresh cycles may be used as CE dummy cycles for initialization. The 64 refresh dummy cycles can be performed before or after the 8 CE dummy cycles. Both dummy cycles must be within AC parameters. See figure 1, below.
- (3) AC measurements assume  $t_T = 5$  ns.
- (4)  $V_{IH}$  (min) and  $V_{IL}$  (max) are reference levels for measuring input signal timing. Transition times are measured between  $V_{IH}$  and  $V_{IL}$ .
- (5) Load = 2 TTL loads and 50 pF.
- (6)  $t_{CEZ}$  (max) and  $t_{OEZ}$  (max) define the time at which the output achieves the open circuit condition and are not referenced to  $V_{OH}$  or  $V_{OL}$ .
- (7)  $t_{WSC} \leq t_{WSC}$  (min), the cycle is a late write cycle.
- (8) A power down self-refresh cycle is initiated when the RFSH input is active low for a period of 40 μs. The refresh interval is about 15.6 μs.

**Figure 1. Power-up Dummy Cycles**

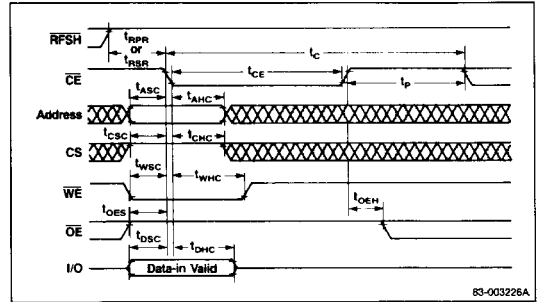


Timing Waveforms

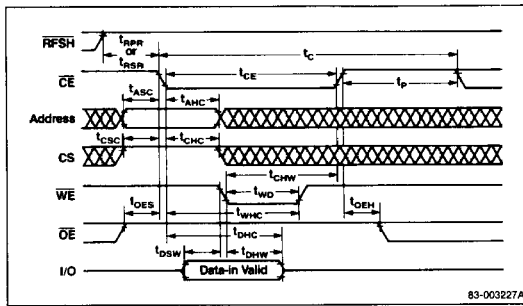
Read Cycle



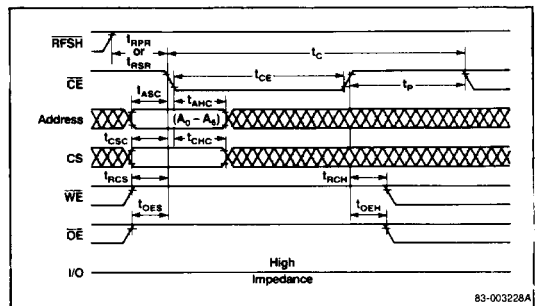
Early Write Cycle



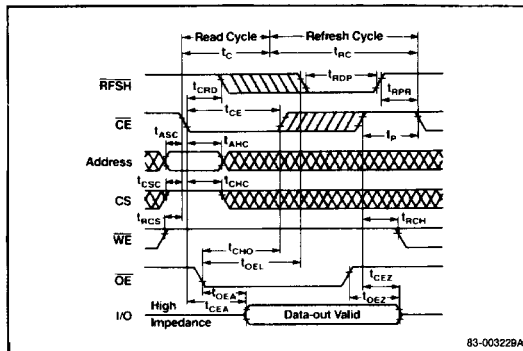
Late Write Cycle



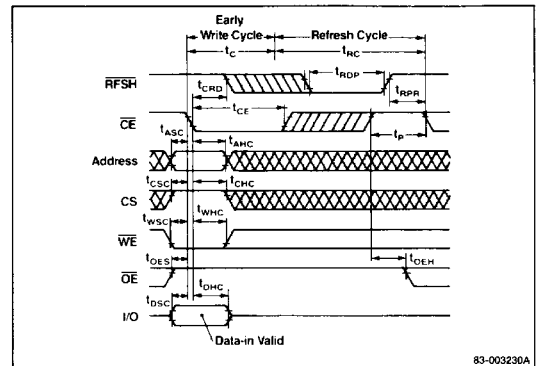
External Refresh Cycle



Pulse Refresh Cycle after Read Cycle Complete

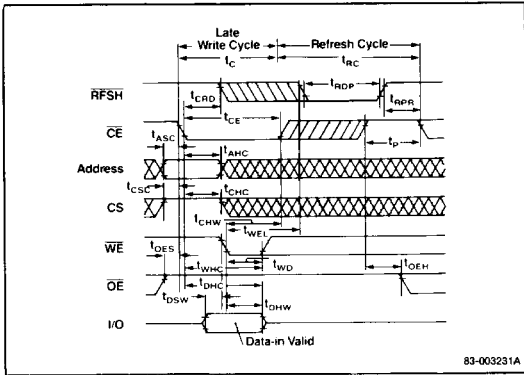


Pulse Refresh Cycle after Early Write Cycle Complete

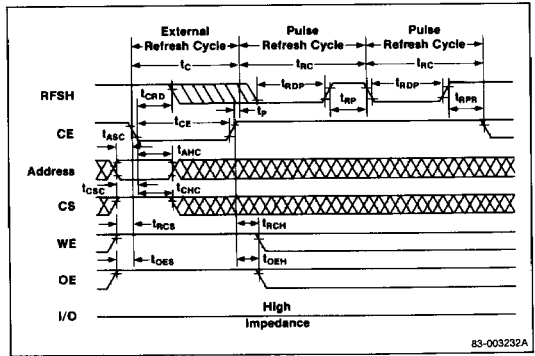


## Timing Waveforms (cont)

### Pulse Refresh Cycle after Late Write Cycle Complete



### Pulse Refresh Cycle after External Refresh Cycle Complete



### Power-down Self Refresh

